CERTIFICATE OF TRANSMISSION OR MAILING
I hereby certify that this correspondence is being facsimile transmitted to the USPTO or deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on the date shown below.
September 1, 2006
Signed Michelle Chan
Michelle Chan

Appl. No.	:	10/796,413	Confirmation No. 9041
Applicant	:	Xiangfeng Duan et al.	
Filed	:	March 10, 2004	
TC/A.U.	:	2891	
Examiner	:	Matthew Reames	
Docket No.	:	01-004100	
Customer No.	:	33140	
Title	:	Nano-enabled Memory Devices and Anisotropic Charge Carrying Arrays	

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

The references cited on the attached form PTO/SB08A-B are being called to the attention of the Examiner. Pursuant to 37 CFR §1.98(a)(2), copies of all foreign patent documents and non US Patent and US Patent application publications are enclosed.

It is respectfully requested that the cited information be expressly considered during the prosecution of this application, and the references be made of record therein and appear among the "references cited" on any patent to issue therefrom.

As provided for by 37 CFR §1.97(g) and (h), no inference should be made that the information and references cited are prior art merely because they are in this statement and no representation is made that a search has been conducted or that this statement encompasses all possible relevant information.

This information disclosure statement is being filed after the mailing date of the first Office Action and more than three months after the filing date, but prior to the mailing of a Notice of Allowance or Final Office Action. Authorization to charge the appropriate fee to the undersigned's deposit account is submitted herewith. Please charge any additional fees or credit any overpayment to Deposit Account No. 50-2336.

Respectfully submitted,

Andrew L. Filler
Reg. No. 44,107

NANOSYS, INC.
2625 Hanover Street
Palo Alto, CA 94304
Tel. (650) 331-2176
Fax (650) 331-2101

(Modified) PTO/SB/08A-B (08-03)
Approved for use through 7/31/2006. OMB 0651-0031

Substitute for form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	**10/796,413**
				Filing Date	**March 10, 2004**
				First Named Inventor	**Duan**
				Art Unit	**2891**
(use as many sheets as necessary)				Examiner Name	**Matthew Reames**
Sheet		of		Attorney Docket Number	**01-004100**

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No.	Document No. Number - Kind Code (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, lines, Where Relevant Passages or Relevant Figures Appeal
	AA	US-5,714,766	02-03-1998	Chen et al.	
	AB	US-5,937,295	08-10-1999	Chen et al.	
	AC	US-6,054,349	04-25-2000	Nakajima et al.	
	AD	US-6,090,666	07-18-2000	Ueda et al.	
	AE	US-6,139,626	10-31-2000	Norris et al.	
	AF	US-6,159,620	12-12-2000	Heath et al.	
	AG	US-6,207,229	03-27-2001	Bawendi et al.	
	AH	US-6,297,095	10-02-2001	Muralidhar et al.	
	AI	US-6,322,901	11-27-2001	Bawendi et al.	
	AJ	US-6,344,403	02-05-2002	Madhukar et al.	
	AK	US-6,413,819	07-02-2002	Zafar et al.	
	AL	US-6,576,291	06-10-2003	Bawendi et al.	
	AM	US-6,586,785	07-01-2003	Flagan et al.	
	AN	US-6,670,670	12-30-2003	Chae et al.	
	AO	US-6,872,645	03-29-2005	Duan et al.	
	AP	US-20030153151	08-14-2003	Choi et al.	
	AQ	US-20040130941	07-08-2004	Kan et al.	
	AR	US-20050072989	04-07-2005	Bawendi et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials	Cite No.	Foreign Patent Document Country Code - Number - Kind Code (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T
	AS	WO-0103208	01-11-2001	Harvard		
	AT	WO-0217362	02-28-2002	Harvard		
	AU	WO-0248701	06-20-2002	Harvard		
	AV	WO-2005017962	02-24-2005	Nanosys		

Examiner Signature		Date Considered	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Substitute for form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	**10/796,413**
				Filing Date	**March 10, 2004**
				First Named Inventor	**Duan**
				Art Unit	**2891**
(use as many sheets as necessary)				Examiner Name	**Matthew Reames**
Sheet		of		Attorney Docket Number	**01-004100**

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and-or country where published.	T
	AW	ATWATER, H.A. "Silicon nanoparticle engineering for novel logic and memory applications" Project Overview, Functional Nanostructures Program, NSF (January 2001)	
	AX	BELL, L.D. et al., "A Radiation-tolerant, low-power non-volatile memory based on silicon nanocrystal quantum dots" Innovative Approaches to Outer Planetary Exploration 2001-2020 (Publication date unknown)	
	AY	BODEFIELD, M.C. et al., "Storage of electrons and holes in self-assumbled InAs quantum dots" *Appl. Phys. Lett.* (1999) 74(13):1839-1841	
	AZ	CASPERSON, J.D. et al., "Materials issues for layered tunnel barrier structures" J. Appl. Phys. (2002) 92(1):261-267	
	BA	CHAE, D-H et al., "Nanocrystal memory cell using high-density SiGe Quantum Dot Array" J Kor. Phys. Soc. (1999) 35:S995-S998	
	BB	CORSO, D. et al., "Localized Charge storage in nanocrystal memories: feasibility of a multi-bit cell" (Publication and Publication date unknown)	
	BC	DE BLAUWE, J. "Nanoparticle Nonvolatile Memory Devices," IEEE Trans. Nanotechnology (2002) 1:72	
	BD	DREXLER, H. et al., "Spectroscopy of quantum levels in charge-tunable InGaAs quantum dots" Phys. Ref. Lett (1994) 73:2252-2255	
	BE	IANNACCONE, G. et al., "Simulation of a quantum-dot flash memory," *J. Appl. Phys.* (1998) 84(9):5032-5036	
	BF	KAN, E. "Technology for self-assembled entities in logic and memory units below the lithography limit" Cornell Nanoscale Facility (Publication date unknown)	
	BG	TAKATA, M. et al. "Fundamental characteristics of new non-volatile memory with extremely high density metal quantum dots" (Publication and Publication Date unknown)	
	BH	TIWARI, S. et al., "Volatile and Non-Volatile Memories in Silicon with Nano-Crystal Storage," IEDM (1995) 95-521	
	BI	TIWARI, S. et al., "A silicon nanocrystals based memory" Appl. Phys. Lett (1996) 68(10:1377-1379	
	BJ	VAMPOLA, K. et al., "Growth and Characterization of metal nanocrystals" Cornell Nanofabrication Facility (Publication date unknown)	
	BK		
	BL		

Examiner Signature		Date Considered	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.